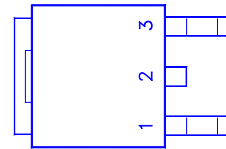
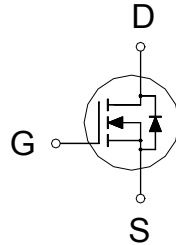


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
200V	325mΩ	10A



1: GATE
2: DRAIN
3: SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	200	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	10	A
	$T_C = 100^\circ\text{C}$		6.3	
Pulsed Drain Current ¹		I_{DM}	26	
Avalanche Current		I_{AS}	6.5	
Avalanche Energy	$L = 1\text{mH}$	E_{AS}	21.1	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	52	W
	$T_C = 100^\circ\text{C}$		20	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	°C / W
Junction-to-Case	$R_{\theta JC}$		2.4	

¹Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	200			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1	2	3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			±100	nA

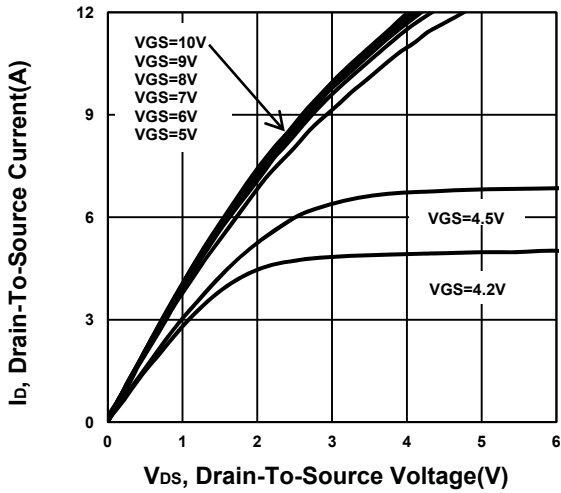
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200V, V_{GS} = 0V$			1	μA
		$V_{DS} = 160V, V_{GS} = 0V, T_J = 125^\circ C$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 5A$		261	325	$m\Omega$
		$V_{GS} = 4.5V, I_D = 5A$		364	440	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 10V, I_D = 5A$		6		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$		372		pF
Output Capacitance	C_{oss}			69		
Reverse Transfer Capacitance	C_{rss}			11		
Total Gate Charge ²	Q_g	$V_{DS} = 160V, I_D = 10A, V_{GS} = 10V$		12.7		nC
Gate-Source Charge ²	Q_{gs}			1.7		
Gate-Drain Charge ²	Q_{gd}			5.5		
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 100V, I_D \cong 10A, V_{GS} = 10V, R_{GEN} = 6\Omega$		10		nS
Rise Time ²	t_r			30		
Turn-Off Delay Time ²	$t_{d(off)}$			24		
Fall Time ²	t_f			35		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ C$)						
Continuous Current ³	I_S				10	A
Forward Voltage ¹	V_{SD}	$I_F = 10A, V_{GS} = 0V$			1	V
Diode Reverse Recovery Time	t_{rr}	$I_F = 10A, di/dt = 100A/\mu s$		103		nS
Diode Reverse Recovery Charge	Q_{rr}			377		nC

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

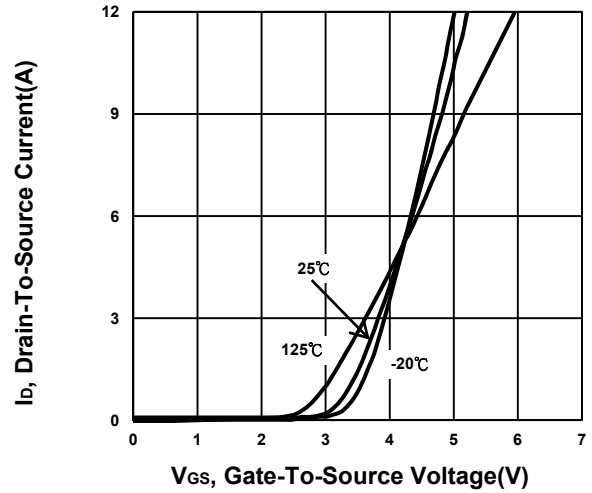
²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

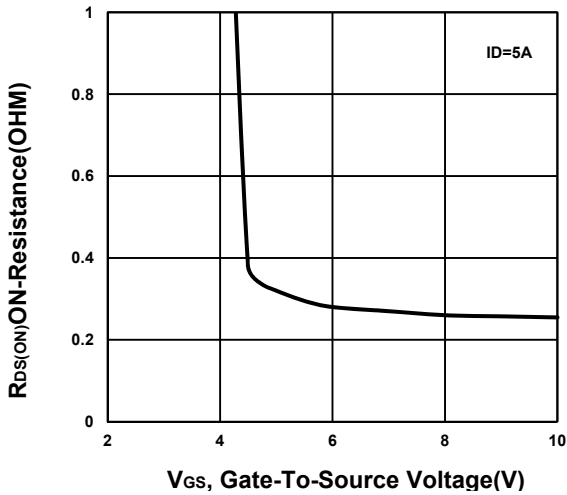
Output Characteristics



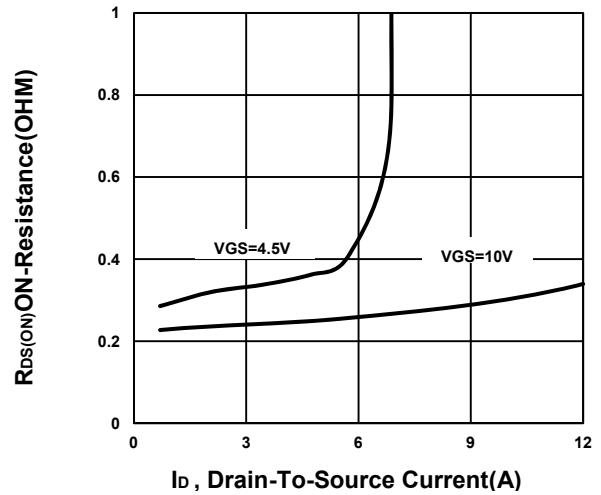
Transfer Characteristics



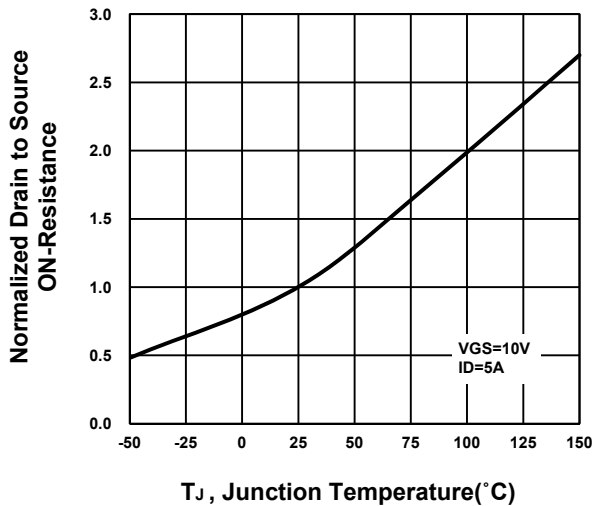
On-Resistance VS Gate-To-Source



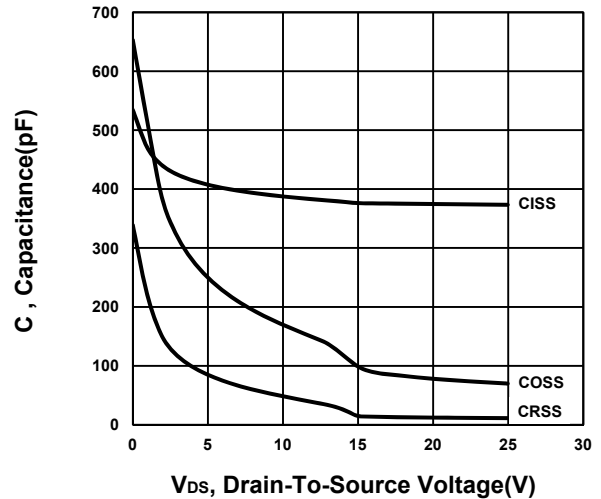
On-Resistance VS Drain Current



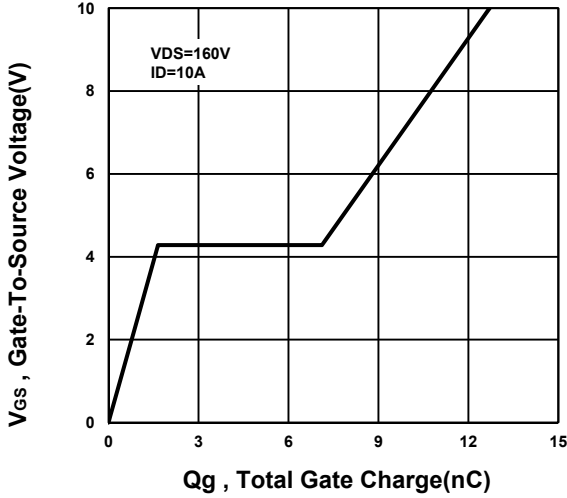
On-Resistance VS Temperature



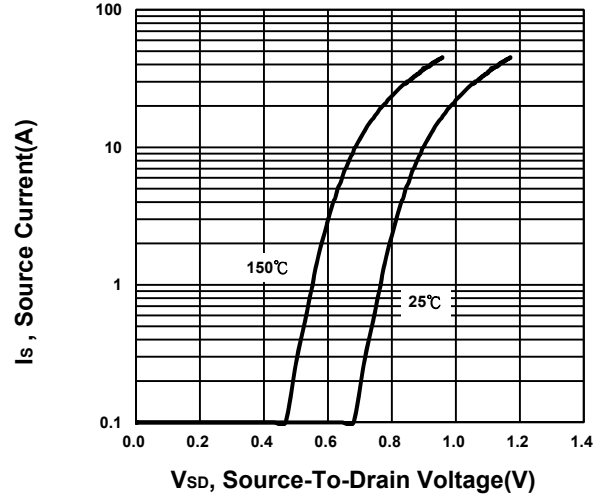
Capacitance Characteristic



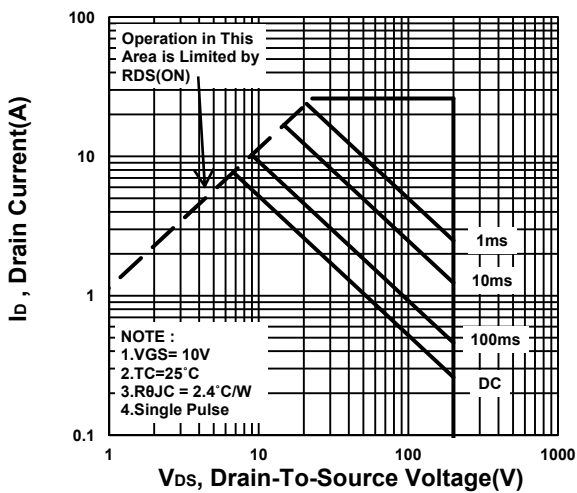
Gate charge Characteristics



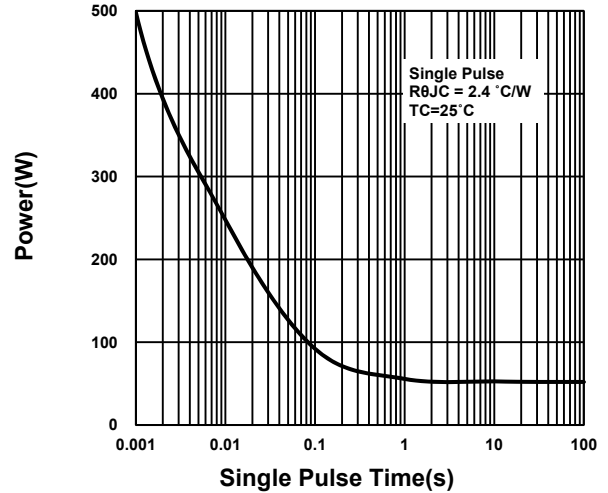
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

